

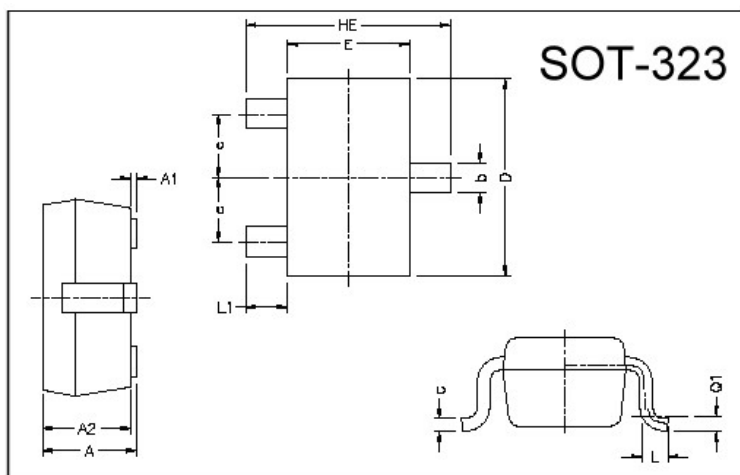
GSMBTA56

PNP SILICON TRANSISTOR

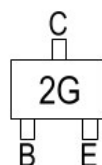
Description

The GSMBTA56 is designed for general purpose amplifier applications.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25°C

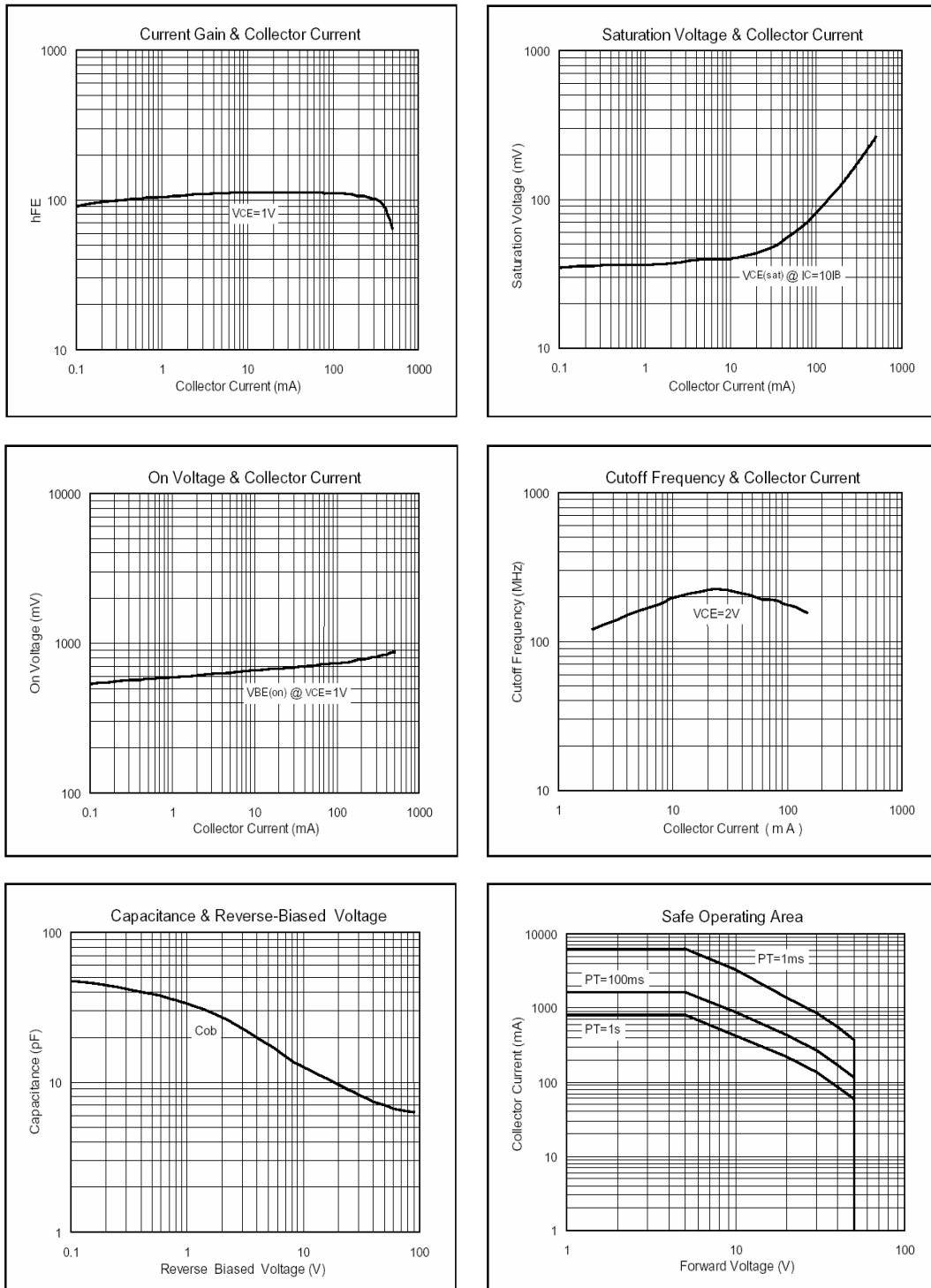
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	-80	V
Collector to Emitter Voltage	VCEO	-80	V
Emitter to Base Voltage	VEBO	-4	V
Collector Current	Ic	-500	mA
Total Power Dissipation	Pd	225	mW

Electrical Characteristics (Ta = 25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-80	-	-	V	Ic=-100uA, IE=0
BVCEO	-80	-	-	V	Ic=-1mA, IB=0
BVEBO	-4	-	-	V	IE=-100uA, IC=0
ICBO	-	-	-100	nA	VCB=-80V, IE=0
ICEO	-	-	-100	nA	VCE=-60V, IB=0
*VCE(sat)	-	-	-250	mV	Ic=-100mA, IB=-10mA
*VBE(on)	-	-	-1.2	V	VCE=-1V, Ic=-100mA
*hFE1	50	-	-		VCE=-1V, Ic=-10mA
*hFE2	50	-	-		VCE=-1V, Ic=-100mA
fT	100	-	-	MHz	VCE=-2V, Ic=-10mA, f=100MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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